

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	16	((first adj type) and (second adj type)) adj4 (TFT "thin film transistor")	US-PGPUB; USPAT	OR	ON	2005/08/02 09:17
S3	0	"2001376587"	US-PGPUB; USPAT; JPO	OR	ON	2005/08/02 09:43
S8	318	miyazawa-toshio.in.	JPO	OR	ON	2005/08/02 09:44
S6	0	"2001376587"	JPO	OR	ON	2005/08/02 09:44
S5	0	"376587"	JPO	OR	ON	2005/08/02 09:44
S4	1	"2001-376587"	US-PGPUB; USPAT; JPO	OR	ON	2005/08/02 09:44
S9	0	JP20010376587	JPO	OR	ON	2005/08/02 09:48
S7	0	"20010376587"	JPO	OR	ON	2005/08/02 09:48
S10	1	JP2001376587	JPO	OR	ON	2005/08/02 10:49
S11	1	JP2003176281	JPO	OR	ON	2005/08/02 10:51
S14	325	S13 and hitachi.as.	JPO	OR	ON	2005/08/02 10:53
S12	1565	tai-mitsuhashi.in. mutsuko-hatano.in. yamaguchi-shinya.in. shiba-kodaira.in. sato-hideo.in.	JPO	OR	ON	2005/08/02 10:53
S15	244	tai-mitsuhashi.in. mutsuko-hatano.in. yamaguchi-shinya.in. shiba-kodaira.in. sato-hideo.in.	US-PGPUB; USPAT	OR	ON	2005/08/02 10:54
S16	264	tai-mitsuhashi.in. hatano-mutsuko.in. yamaguchi-shinya.in. shiba-kodaira.in. sato-hideo.in.	US-PGPUB; USPAT	OR	ON	2005/08/02 10:55
S19	145	S18 and thin adj film	US-PGPUB; USPAT	OR	ON	2005/08/02 10:57
S17	190	S16 and @pd<"20030206"	US-PGPUB; USPAT	OR	ON	2005/08/02 10:57
S20	0	peak-to-valley with "20nm"	US-PGPUB; USPAT	OR	ON	2005/08/02 14:12
S18	690	peak-to-valley with height	US-PGPUB; USPAT	OR	ON	2005/08/02 14:12
S22	1206	349/43.ccls.	US-PGPUB; USPAT	OR	ON	2005/08/02 14:15
S23	2	S22 and ((peak adj2 valley) peak-to-valley)	US-PGPUB; USPAT	OR	ON	2005/08/02 14:16
S24	158	((peak adj2 valley) peak-to-valley) and (TFT (thin adj film adj transistor))	US-PGPUB; USPAT	OR	ON	2005/08/02 14:24

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S26	2	((peak adj2 valley) peak-to-valley) and 349/43.ccls.	US-PGPUB; USPAT	OR	ON	2005/08/02 14:33
S25	67	((peak adj2 valley) peak-to-valley) and (TFT (thin adj film adj transistor)) and polycrystalline	US-PGPUB; USPAT	OR	ON	2005/08/02 14:33
S28	104	((peak with valley) peak-to-valley) and grain adj size and polycrystalline	US-PGPUB; USPAT	OR	ON	2005/08/02 15:51
S29	35	((peak with valley) peak-to-valley) and grain adj size and polycrystalline and (TFT "thin film transistor")	US-PGPUB; USPAT	OR	ON	2005/08/02 15:52
S30	7	("5270567" "5757445" "5798744" "5851440" "5926702" "6011277" "6211553").PN. OR ("6476788").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 16:03
S32	3	S31 and (TFT "thin film transistor")	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 16:05
S34	508	polycrystalline and grain adj size and orientation and (TFT "thin film transistor")	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 16:43
S33	108	polycrystalline and grain adj diameter and orientation and (TFT "thin film transistor")	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 16:43
S35	44	polycrystalline and (grain adj size) with ("100" adj nm)and orientation and (TFT "thin film transistor")	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 16:47
S36	2	10/143192	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:45
S38	5	peak-to-valley adj height with "5" adj nm	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:58
S31	205	peak-to-valley adj height and current	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:58
S42	1	peak-to-valley adj height with "2" adj nm	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:59
S41	0	peak-to-valley adj height with "1" adj nm	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:59
S40	0	peak-to-valley adj height with "3" adj nm	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:59

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S39	0	peak-to-valley adj height with "4" adj nm	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 17:59
S44	35	S43 and "thin film transistor"	US-PGPUB; USPAT	OR	ON	2005/08/02 18:07
S43	492	((peak with valley) peak-to-valley) with "nm"	US-PGPUB; USPAT	OR	ON	2005/08/02 18:07
S27	4	((peak with valley) peak-to-valley) and 349/43.ccls.	US-PGPUB; USPAT	OR	ON	2005/08/02 18:07
S37	4	09/790545	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 18:31
S47	127	S46 and (TFT "thin film transistor")	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 18:34
S46	145	grain with scanning adj direction	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 18:34
S45	7	polycrystalline adj silicon and grain adj size and peak-to-valley	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/02 18:34
S48	70	pixel with TFT same grain adj size	US-PGPUB; USPAT	OR	ON	2005/08/03 10:24
S49	30	peak-to-valley same (leak leakage) adj current	US-PGPUB; USPAT	OR	ON	2005/08/03 10:25
S50	17	peak-to-valley same (leak leakage) adj current and (polysilicon polycrystalline)	US-PGPUB; USPAT	OR	ON	2005/08/03 10:26
S53	0	peak-to-valley same (switch\$ adj speed) and (polysilicon polycrystalline)	US-PGPUB; USPAT	OR	ON	2005/08/03 10:27
S52	0	peak-to-valley same (switching adj speed) and (polysilicon polycrystalline)	US-PGPUB; USPAT	OR	ON	2005/08/03 10:27
S51	71807	peak-to-valley same (switching adj speed) current and (polysilicon polycrystalline)	US-PGPUB; USPAT	OR	ON	2005/08/03 10:27
S21	122	peak-to-valley with "20"	US-PGPUB; USPAT	OR	ON	2005/08/03 10:27
S55	510	(roughness peak-to-valley) and (polysilicon polycrystalline) and (TFT "thin film transistor")	US-PGPUB; USPAT	OR	ON	2005/08/03 10:30
S54	12	peak-to-valley and (polysilicon polycrystalline) and (TFT "thin film transistor")	US-PGPUB; USPAT	OR	ON	2005/08/03 10:30

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S56	508	roughness and (polysilicon polycrystalline) and (TFT "thin film transistor")	US-PGPUB; USPAT	OR	ON	2005/08/03 10:31
S57	409	roughness and (polysilicon polycrystalline) and (TFT "thin film transistor") and (speed current)	US-PGPUB; USPAT	OR	ON	2005/08/03 10:32
S58	53	roughness same (speed current) and (polysilicon polycrystalline) and (TFT "thin film transistor")	US-PGPUB; USPAT	OR	ON	2005/08/03 10:48
S59	2	10/226110	US-PGPUB; USPAT	OR	ON	2005/08/03 10:49
S60	3	10/226110 "6621103".pn.	US-PGPUB; USPAT	OR	ON	2005/08/03 10:50
S61	5	10/226110 10/112929	US-PGPUB; USPAT	OR	ON	2005/08/03 12:19
S62	1	"20020102823"	US-PGPUB; USPAT	OR	ON	2005/08/03 12:25
S63	772	grain adj diameter with nm	US-PGPUB; USPAT	OR	ON	2005/08/03 12:26
S64	212	S63 and (polysilicon polycrystalline)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:27
S65	28	(US-20030107564-\$ or US-20040257486-\$ or US-20040038600-\$ or US-20050112850-\$ or US-20020142567-\$ or US-20040115953-\$ or US-20040259326-\$ or US-20040145001-\$ or US-20020102823-\$ or US-20020158829-\$ or US-20030049874-\$ or US-20050140283-\$ or US-20050088381-\$ or US-20040038501-\$ or US-20040171236-\$).did. or (US-6476788-\$ or US-6535257-\$ or US-6740938-\$ or US-6636280-\$ or US-6586791-\$ or US-6911698-\$ or US-6806498-\$ or US-6716726-\$ or US-6690064-\$ or US-5851440-\$ or US-6887724-\$ or US-6479837-\$ or US-6621103-\$).did.	US-PGPUB; USPAT	OR	ON	2005/08/03 12:28
S68	3148	S67 and (transistor TFT)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:34
S66	20	S65 and (grain adj (size diameter))	US-PGPUB; USPAT	OR	ON	2005/08/03 12:34
S70	948	S69 and (transistor TFT)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:35

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S67	6759	grain adj size and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:35
S69	1662	large with grain adj size and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:38
S71	225	large with grain adj diameter and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:40
S72	212	grain adj diameter with nm and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:53
S73	7	grain adj diameter with ("900" "800" "700" "600") adj nm and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 12:56
S74	40	grain adj size with ("900" "800" "700" "600") adj nm and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 13:13
S75	0	grain adj size with ("900" "800" "700" "600") and large adj nm and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 13:14
S76	26	grain adj size with (large and ("900" "800" "700" "600") adj nm) and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2005/08/03 13:30
S77	1	"20020158298"	US-PGPUB; USPAT	OR	ON	2005/08/03 13:36
S79	1	"6479837".pn.	US-PGPUB; USPAT	OR	ON	2005/08/03 13:47
S78	1	"20040038438"	US-PGPUB; USPAT	OR	ON	2005/08/03 13:47
S80	1	"20040038438"	US-PGPUB; USPAT	OR	ON	2005/08/03 13:56
S81	1	10/652511	US-PGPUB; USPAT	OR	ON	2005/08/19 09:43
S82	60	second adj (TFT transistor) and "349"/\$.ccls. and polycrystal\$6	US-PGPUB; USPAT	OR	ON	2006/02/18 19:06
S83	89	349/48.cccls.	US-PGPUB; USPAT	OR	ON	2006/02/18 19:39
S85	481	"349"/\$.cccls. and (second adj (tft transistor thin adj film))	US-PGPUB; USPAT	OR	ON	2006/02/18 19:45
S84	55	349/48.cccls. and amorphous	US-PGPUB; USPAT	OR	ON	2006/02/18 19:45
S86	7	("5430462" "5550659" "5610629" "5771039").PN. OR ("6028581").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/18 19:47
S87	42	("5042916" "5161237" "5193018" "5194974" "5349366").PN. OR ("5828429").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/18 21:19

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S88	1	10/772431	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/18 21:40
S89	0	"349"/\$.ccls. and (switching adj speed and reliability)	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/18 21:41
S90	68	"349"/\$.ccls. and (switching adj speed and reliability)	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/18 21:42
S92	148	"349"/\$.ccls. and sampling and buffer and (shift shifter)	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/18 21:46
S91	6	"349"/\$.ccls. and (transistor with switching adj speed and reliability)	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/18 21:46
S93	2473	(TFT thin adj film adj transistor) with (uniform\$)	US-PGPUB; USPAT	OR	ON	2006/03/03 16:50
S94	2216	(TFT thin adj film adj transistor) with (uniform\$) and (LCD liquid adj crystal)	US-PGPUB; USPAT	OR	ON	2006/03/03 16:53
S96	44	pixel with ((TFT thin adj film adj transistor) with (speed and (defect reliabl\$5)))	US-PGPUB; USPAT	OR	ON	2006/03/03 16:59
S97	44	pixel with (TFT thin adj film adj transistor) with (speed and (defect reliabl\$5))	US-PGPUB; USPAT	OR	ON	2006/03/03 17:05
S98	1	"6512504".pn.	US-PGPUB; USPAT	OR	ON	2006/03/03 17:27
S99	340	pixel adj tft and grain adj size	US-PGPUB; USPAT	OR	ON	2006/03/03 17:28
S100	17	pixel adj tft same grain adj size	US-PGPUB; USPAT	OR	ON	2006/03/03 17:31
S101	1	"20020158298"	US-PGPUB; USPAT	OR	ON	2006/03/03 17:32
S102	1	"6673639".pn.	US-PGPUB; USPAT	OR	ON	2006/03/03 17:35
S103	2925	grain adj size with (" .mu.m" nm)	US-PGPUB; USPAT	OR	ON	2006/03/03 18:31
S104	876	grain adj size with (" .mu.m" nm) and polycrystal\$6	US-PGPUB; USPAT	OR	ON	2006/03/03 18:32
S106	9	grain adj size same pixel adj tft and (roughness peak-to-valley peak adj to adj valley)	US-PGPUB; USPAT	OR	ON	2006/03/03 19:22
S107	1	"6479837".pn.	US-PGPUB; USPAT	OR	ON	2006/03/03 19:23

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S10 9	6	(grain adj size) with ("300" "400" "500" "600" "700" "800" "900") adj nm and "349"/\$.ccls.	US-PGPUB; USPAT	OR	ON	2006/03/03 19:42
S11 0	18	(grain adj size) with ("300" "400" "500" "600" "700" "800" "900") adj nm and pixel adj (tft transistor)	US-PGPUB; USPAT	OR	ON	2006/03/03 19:43
S11 1	642	(grain adj size) with ("300" "400" "500" "600" "700" "800" "900") and roughness	US-PGPUB; USPAT	OR	ON	2006/03/03 19:44
S11 2	104	S111 and polycrystal\$5	US-PGPUB; USPAT	OR	ON	2006/03/03 19:46
S11 3	3	WO9745827	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/03 19:47
S11 6	1	"20040005743"	US-PGPUB; USPAT; USOCR	OR	ON	2006/03/03 19:57
S11 5	0	"2004005743"	US-PGPUB; USPAT; USOCR	OR	ON	2006/03/03 19:57
S11 4	2	("6150203" "6331496").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/03/03 19:57
S95	659	(TFT thin adj film adj transistor) with (speed and (defect reliabl\$5))	US-PGPUB; USPAT	OR	ON	2006/03/03 20:03
S11 8	84	peak-to-valley and polysilicon	US-PGPUB; USPAT	OR	ON	2006/03/03 20:09
S11 7	4	roughness with (off adj current) and tft	US-PGPUB; USPAT	OR	ON	2006/03/03 20:09
S11 9	82	peak-to-valley and polycrystal\$ adj silicon	US-PGPUB; USPAT	OR	ON	2006/03/03 20:12
S12 0	436	roughness with nm and polycrystal\$ adj silicon	US-PGPUB; USPAT	OR	ON	2006/03/03 20:13
S12 1	718	roughness with ("20" adj nm)	US-PGPUB; USPAT	OR	ON	2006/03/03 20:29
S12 2	35	S121 and polycrystalline adj silicon	US-PGPUB; USPAT	OR	ON	2006/03/03 20:45
S12 3	2	"20020145694"	US-PGPUB; USPAT	OR	ON	2006/03/04 15:00
S12 4	255	grain adj size same ((off leakage) adj current)	US-PGPUB; USPAT	OR	ON	2006/03/04 15:13
S12 6	1	10/485790	US-PGPUB; USPAT	OR	ON	2006/03/04 15:34

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S12 8	0	makimura-shingo.in. and hashimoto-makoto.in..	JPO	OR	ON	2006/03/04 15:36
S13 2	1	"2002166380"	JPO	OR	ON	2006/03/04 15:37
S13 1	0	JP2002166380	JPO	OR	ON	2006/03/04 15:37
S13 0	0	JP2002-166380	JPO	OR	ON	2006/03/04 15:37
S12 9	4	makimura-shingo.in.	US-PGPUB; USPAT	OR	ON	2006/03/04 15:37
S13 3	0	"20033023765"	JPO	OR	ON	2006/03/04 15:45
S12 7	10	makimura-shingo.in.	JPO	OR	ON	2006/03/04 15:45
S13 6	0	"\$3023765"	JPO	OR	ON	2006/03/04 15:46
S13 5	0	"3023765"	JPO	OR	ON	2006/03/04 15:46
S13 4	0	"2003-3023765"	JPO	OR	ON	2006/03/04 15:46
S13 8	8	@ad="20020706"	JPO	OR	ON	2006/03/04 15:47
S13 7	0	ad="20020706"	JPO	OR	ON	2006/03/04 15:47
S12 5	38	((grain adj size) with ("nm" "mm" ".mu.m")) same ((off leakage) adj current)	US-PGPUB; USPAT	OR	ON	2006/03/04 16:05
S13 9	51	((grain adj size) with ("nm" "mm" "mu.m")) same ((off leakage) adj current)	US-PGPUB; USPAT	OR	ON	2006/03/04 16:08
S14 1	1124	((grain adj size) with ("nm" "mm" "mu.m")) and polycrystall\$5 and (TFT thin adj film)	US-PGPUB; USPAT	OR	ON	2006/03/04 16:09
S14 0	1995	((grain adj size) with ("nm" "mm" "mu.m")) and polycrystall\$5	US-PGPUB; USPAT	OR	ON	2006/03/04 16:09
S14 2	902	((grain adj size) with ("nm" "mm" "mu.m")) and polycrystall\$5 and (TFT thin adj film) and @ad<"20030620"	US-PGPUB; USPAT	OR	ON	2006/03/04 16:15
S14 3	209	((grain adj size) with ("nm" "mm" "mu.m")) and polycrystall\$5 and (TFT thin adj film) and @ad<"20030620" and pixel	US-PGPUB; USPAT	OR	ON	2006/03/04 16:25

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S14 4	48	((grain adj size) with ("nm" "mm" "mu.m")) and polycrystall\$5 and (TFT thin adj film) and @ad<"20030620" and pixel and roughness	US-PGPUB; USPAT	OR	ON	2006/03/04 16:55
S14 6	20	((grain adj size) with ("nm" "mm" "mu.m")) and polycrystall\$5 and roughness with "20 nm"	US-PGPUB; USPAT	OR	ON	2006/03/04 16:58
S14 5	26	((grain adj size) with ("nm" "mm" "mu.m")) and polycrystall\$5 and (TFT thin adj film) and @ad<"20030620" and pixel and roughness with "nm"	US-PGPUB; USPAT	OR	ON	2006/03/04 16:58
S10 8	1	"20020142567"	US-PGPUB; USPAT	OR	ON	2006/03/04 17:20
S14 9	173	pixel adj TFT with reliability	US-PGPUB; USPAT	OR	ON	2006/03/04 17:23
S14 8	0	pixel adj TFT with reliability	US-PGPUB; USPAT	OR	ON	2006/03/04 17:23
S14 7	29	peak-to-valley with "nm" and polycrystal\$	US-PGPUB; USPAT	OR	ON	2006/03/04 17:23
S15 0	111	pixel adj TFT with reliability and (polysilicon polycrystall\$)	US-PGPUB; USPAT	OR	ON	2006/03/04 17:25
S15 1	7	roughness same "off current" and (polycrystalline polysilicon)	US-PGPUB; USPAT	OR	ON	2006/03/04 18:03
S15 2	1	"6512247".pn.	US-PGPUB; USPAT	OR	ON	2006/03/04 18:18
S15 3	1	"20040005743"	US-PGPUB; USPAT	OR	ON	2006/03/04 18:19
S15 4	1	"6479837".pn.	US-PGPUB; USPAT	OR	ON	2006/03/04 18:25
S15 5	364	driv\$5 adj (TFT thin adj film) same (mobility defect)	US-PGPUB; USPAT	OR	ON	2006/03/04 18:26
S15 6	7	driv\$5 adj (TFT thin adj film) same (mobility and defect)	US-PGPUB; USPAT	OR	ON	2006/03/04 18:27
S15 7	17	driv\$5 adj (TFT thin adj film) same (mobilit\$ and defect\$)	US-PGPUB; USPAT	OR	ON	2006/03/04 18:29
S15 8	40	driv\$5 adj (TFT thin adj film) same (mobilit\$ and (defect\$ yield))	US-PGPUB; USPAT	OR	ON	2006/03/04 18:43
S16 0	0	"6512247.pn"	US-PGPUB; USPAT	OR	ON	2006/03/04 18:49
S15 9	20	(roughness with "nm") with mobility	US-PGPUB; USPAT	OR	ON	2006/03/04 18:49
S16 1	1	"6512247".pn.	US-PGPUB; USPAT	OR	ON	2006/03/05 13:10

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S16 3	1664	S162 and (TFT thin adj film)	US-PGPUB; USPAT	OR	ON	2006/03/05 13:36
S16 2	3035	(polysilicon polycrystalline) and (gate adj insulat\$5) with (material and thickness)	US-PGPUB; USPAT	OR	ON	2006/03/05 13:49
S16 4	255	(polysilicon polycrystalline) and (gate adj insulat\$5) adj3 (material and thickness)	US-PGPUB; USPAT	OR	ON	2006/03/05 13:52
S16 6	5584	(polysilicon polycrystalline) and (gate adj insulat\$5) adj3 (silicon (oxide dioxide))	US-PGPUB; USPAT	OR	ON	2006/03/05 13:53
S16 5	255	(polysilicon polycrystalline) and (gate adj insulat\$5) adj3 (materials and thickness)	US-PGPUB; USPAT	OR	ON	2006/03/05 13:53
S16 7	2730	(polysilicon polycrystalline) and (gate adj insulat\$5) adj3 (silicon adj (oxide dioxide))	US-PGPUB; USPAT	OR	ON	2006/03/05 13:55
S16 8	235	(polysilicon polycrystalline) and (gate adj insulat\$5) with (silicon adj (oxide and nitride)) and "349"/\$. ccls.	US-PGPUB; USPAT	OR	ON	2006/03/05 14:21
S16 9	3	peripheral with (level and buffer and sampling) and "349"/\$.ccls.	US-PGPUB; USPAT	OR	ON	2006/03/05 14:25
S17 1	1	"6512247".pn.	US-PGPUB; USPAT	OR	ON	2006/03/05 15:04
S17 0	42	peripheral with (buffer) and "349"/\$.ccls.	US-PGPUB; USPAT	OR	ON	2006/03/05 15:04
S2	1	10/772431	US-PGPUB; USPAT	OR	ON	2006/10/27 16:24
S17 2	1	"6479837".pn.	US-PGPUB; USPAT	OR	ON	2006/10/27 16:26
S17 3	94	"349"/\$.CCLS. and roughness with "nm"	US-PGPUB; USPAT	OR	ON	2006/10/27 16:33
S17 4	2	"349"/\$.CCLS. and roughness with "nm" same grain	US-PGPUB; USPAT	OR	ON	2006/10/27 16:34
S17 5	71	TFT and roughness with "nm" same grain	US-PGPUB; USPAT	OR	ON	2006/10/27 16:47
S17 7	1400	349/43.cccls.	US-PGPUB; USPAT	OR	ON	2006/10/27 17:44
S17 6	1	"6512504".pn.	US-PGPUB; USPAT	OR	ON	2006/10/27 17:44
L4	1592	349/43,48.cccls.	US-PGPUB; USPAT	OR	ON	2007/04/15 19:23
L3	1513	349/43.cccls.	US-PGPUB; USPAT	OR	ON	2007/04/15 19:23

EAST Search History

S10 5	266	grain adj size with (*.mu.m" nm) and polycrystal\$6 and (TFT thin adj film adj transistor)	US-PGPUB; USPAT	OR	ON	2007/04/15 19:28
L5	6	(grain adj size with (*.mu.m" nm) and polycrystal\$6 and (TFT thin adj film adj transistor)).clm.	US-PGPUB	OR	ON	2007/04/15 19:28